



Final Product/Process Change Notification
Generic Copy

07-MAY-2003

SUBJECT: ON Semiconductor Final Product/Process Change Notification 12910

TITLE: Additional Wafer Capacity for 60V N-Channel TMOS Products at Phenitec

EFFECTIVE DATE: 07-Jul-2003

AFFECTED CHANGE CATEGORY(S): Subcontractor Fab Site

AFFECTED PRODUCT DIVISION: MOS Power Products Div

ADDITIONAL RELIABILITY DATA: Contact you local ON Semiconductor Sales Representative or Keith Stapley <RXNN90@onsemi.com>

SAMPLES: Contact you local ON Semiconductor Sales Representative or Spiro Zefferys <FFMYGQ@onsemi.com>

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact Sales Representative or Karen Wright <RD9130 @onsemi.com >

NOTIFICATION TYPE:
Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is the final notification to announce that ON Semiconductor is adding wafer fabrication capacity for the listed 60V, N-Channel TMOS devices at Phenitec Semiconductor Corporation located in Okayama, Japan. The Phenitec facility has been producing TMOS products for ON Semiconductor since 1999 and is a preferred wafer fab supplier. Phenitec is an ISO9002 and QS9000 certified facility. Electrical performance and datasheet specifications of the devices being transferred to Phenitec will not change.

**Final Product/Process Change Notification 12910****RELIABILITY DATA SUMMARY :**

Qualification Results Analysis:

No qualification related anomalies were observed during reliability testing.

Stress Test summary for NTD32N06:

HTRB: TA = +150DegC, Vdss = 48V - 0/240 units at 1008 Hours

HTGB: TA = +150DegC, Vgss = 20V - 0/239 units at 1008 Hours

H3TRB-PC: 85DegC / 85% RH, Vdss = 48V - 0/240 units at 1008 Hours

IOL-PC: TA = 25DegC, Delta Tj ~ 100DegC - 0/239 units at 15000 cycles

Temperature Cycle-PC: Air to Air; -65DegC to +150DegC - 0/240 units at 1000 cycles

H3TRB, IOL, Temperature Cycle units also passed Moisture Sensitivity Level 1 testing.

Electrostatic Discharge Test Results:

ESD sensitivity testing has demonstrated that NTD32N06 meets or exceeds:

- HBM = Class 1 - <2000 V

- MM = Class B - >200 V

- CDM = >2000 V

ELECTRICAL CHARACTERISTIC SUMMARY: Available upon request.

CHANGED PART IDENTIFICATION: N/A

AFFECTED DEVICE LIST (WITHOUT SPECIALS)**PART**

NTB18N06
NTB18N06L
NTB18N06LT4
NTB18N06LT4G
NTB18N06T4
NTB22N06L
NTB22N06LT4
NTB27N06L
NTB27N06LT4
NTB45N06
NTB45N06L
NTB45N06LT4
NTB45N06T4
NTB75N06
NTB75N06T4
NTC3055L104
NTC3055L104TR
NTC3055L104WP
NTC45N06
NTC45N06TR
NTC45N06WP

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NTD15N06
NTD15N06-001
NTD15N06L
NTD15N06L-001
NTD15N06LT4
NTD15N06T4
NTD18N06L
NTD18N06L-001
NTD18N06LT4
NTD20N06
NTD20N06-001
NTD20N06L
NTD20N06L-001
NTD20N06LT4
NTD20N06T4
NTD24N06L-001
NTD3055-094
NTD3055-094-1
NTD3055-094T4
NTD3055-150
NTD3055-150-1
NTD3055-150T4
NTD3055L104
NTD3055L104-001
NTD3055L104T4
NTD32N06
NTD32N06-001
NTD32N06L
NTD32N06L-001
NTD32N06LT4
NTD32N06T4
NTF3055-100T1
NTF3055-100T3
NTF3055-100T3LF
NTF3055-160T1
NTF3055-160T3
NTF3055-160T3LF
NTF3055L108T1
NTF3055L108T3
NTF3055L108T3LF
NTP18N06
NTP18N06L
NTP22N06L
NTP27N06
NTP27N06L
NTP45N06
NTP45N06L
NTP75N06